Quad 3-State Noninverting Buffers

High-Performance Silicon-Gate CMOS

The MC74HC125A and MC74HC126A are identical in pinout to the LS125 and LS126. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The HC125A and HC126A noninverting buffers are designed to be used with 3–state memory address drivers, clock drivers, and other bus–oriented systems. The devices have four separate output enables that are active–low (HC125A) or active–high (HC126A).

- Output Drive Capability: 15 LSTTL Loads
- · Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- · High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 72 FETs or 18 Equivalent Gates

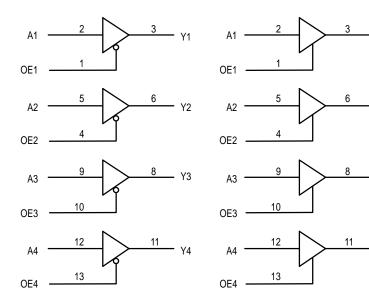
LOGIC DIAGRAM

HC125A Active-Low Output Enables

HC126A Active-High Output Enables

Y2

Y3



PIN 14 = V_{CC} PIN 7 = GND

MC74HC125A MC74HC126A



N SUFFIX

PLASTIC PACKAGE CASE 646-06



D SUFFIX

SOIC PACKAGE CASE 751A-03

ORDERING INFORMATION

MC74HCXXXAN Plastic MC74HCXXXAD SOIC



OE2 L	4	11	∐ Y4
A2 [5	10	OE3
Y2 [6	9	A3
GND [7	8	Y3

FUNCTION TABLE

HC125A				
Inputs Output				
A OE		Υ		
H L		Н		
L	L	L		
X	Н	Z		

_	_	_		
X	Н	Z		
X = d	on't c	are	_	
Z = h	igh im	pedance		

REV 6

HC126A				
Inputs Output				
Α	OE	Y		
Н	Н	Н		
L	Н	L		
Х	L	Z		

₩ MOTOROLA

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
VCC	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	- 1.5 to V _{CC} + 1.5	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
l _{in}	DC Input Current, per Pin	± 20	mA
l _{out}	DC Output Current, per Pin	± 35	mA
Icc	DC Supply Current, V _{CC} and GND Pins	± 75	mA
PD	Power Dissipation in Still Air Plastic DIP† SOIC Package†	750 500	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq VCC. Unused inputs must always be tied to an appropriate logic voltage

level (e.g., either GND or V_{CC}). Unused outputs must be left open.

SOIC Package: -7 mW/ $^{\circ}$ C from 65° to 125° C

For high frequency or heavy load considerations, see Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Max	Unit
VCC	DC Supply Voltage (Referenced to GND)			6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)			Vcc	V
TA	Operating Temperature, All Package Types			+ 125	°C
t _r , t _f	Input Rise and Fall Time (Figure 1)	V _{CC} = 2.0 V V _{CC} = 4.5 V V _{CC} = 6.0 V	0 0 0	1000 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Test Conditions	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
VIH	Minimum High–Level Input Voltage	$V_{Out} = V_{CC} - 0.1 \text{ V}$ $ I_{Out} \le 20 \mu\text{A}$	2.0 4.5 6.0	1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V
VIL	Maximum Low-Level Input Voltage	$V_{Out} = 0.1 \text{ V}$ $ I_{Out} \le 20 \mu\text{A}$	2.0 4.5 6.0	0.5 1.35 1.8	0.5 1.35 1.8	0.5 1.35 1.8	V
VOH	Minimum High–Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out} \le 20 \mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$V_{in} = V_{IH}$ $ I_{out} \le 6.0 \text{ mA}$ $ I_{out} \le 7.8 \text{ mA}$	4.5 6.0	3.98 5.48	3.84 5.34	3.7 5.2	
VOL	Maximum Low–Level Output Voltage	$V_{in} = V_{IL}$ $ I_{Out} \le 20 \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$V_{in} = V_{IL}$ $ I_{out} \le 6.0 \text{ mA}$ $ I_{out} \le 7.8 \text{ mA}$	4.5 6.0	0.26 0.26	0.33 0.33	0.4 0.4	
lin	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
loz	Maximum Three–State Leakage Current	Output in High–Impedance State $V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	6.0	± 0.5	± 5.0	± 10	μΑ
ICC	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND I _{out} = 0 μA	6.0	4.0	40	160	μА

NOTE: Information on typical parametric values can be found in Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

^{*} Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

[†]Derating — Plastic DIP: - 10 mW/°C from 65° to 125°C

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_f = t_f = 6.0 \text{ ns}$)

			Gu	Guaranteed Limit		
Symbol	Parameter	v _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 3)	2.0 4.5 6.0	90 18 15	115 23 20	135 27 23	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Output Enable to Y (Figures 2 and 4)	2.0 4.5 6.0	120 24 20	150 30 26	180 36 31	ns
tPZL, tPZH	Maximum Propagation Delay, Output Enable to Y (Figures 2 and 4)	2.0 4.5 6.0	90 18 15	115 23 20	135 27 23	ns
tTLH, tTHL	Maximum Output Transition Time, Any Output (Figures 1 and 3)	2.0 4.5 6.0	60 12 10	75 15 13	90 18 15	ns
C _{in}	Maximum Input Capacitance	_	10	10	10	pF
C _{out}	Maximum Three–State Output Capacitance (Output in High–Impedance State)		15	15	15	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the Motorola High–Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Per Buffer)*	45	pF

^{*} Used to determine the no–load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}. For load considerations, see Chapter 2 of the Motorola High–Speed CMOS Data Book (DL129/D).

3

SWITCHING WAVEFORMS

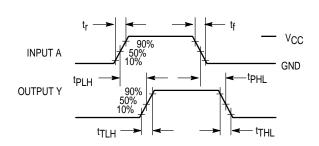


Figure 1.

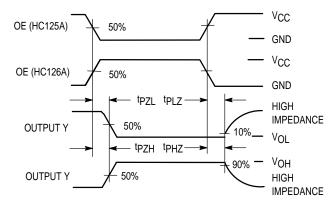
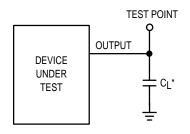
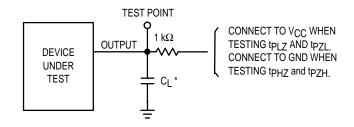


Figure 2.



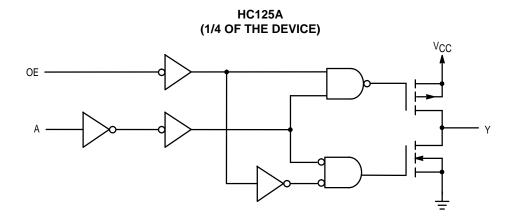
^{*} Includes all probe and jig capacitance

Figure 3. Test Circuit

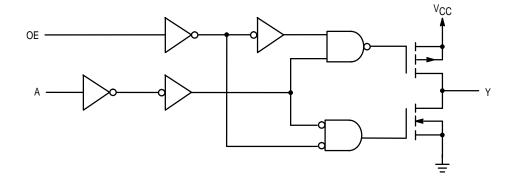


* Includes all probe and jig capacitance

Figure 4. Test Circuit

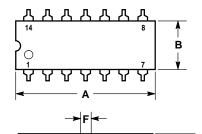


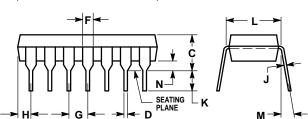
HC126A (1/4 OF THE DEVICE)



OUTLINE DIMENSIONS

N SUFFIX PLASTIC DIP PACKAGE CASE 646-06 ISSUE L





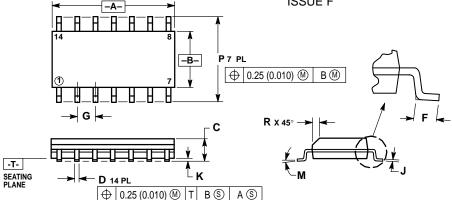
NOTES:

- LEADS WITHIN 0.13 (0.005) RADIUS OF TRUE
 POSITION AT SEATING PLANE AT MAXIMUM
 MATERIAL CONDITION.
- DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
- DIMENSION B DOES NOT INCLUDE MOLD FLASH.
- 4. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.715	0.770	18.16	19.56
В	0.240	0.260	6.10	6.60
С	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100	BSC	2.54	BSC
Н	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.300	BSC	7.62 BSC	
М	0°	10°	0° 10	
N	0.015	0.039	0.39	1.01

D SUFFIX

PLASTIC SOIC PACKAGE CASE 751A-03 ISSUE F



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE
- 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

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MC74HC125A/D